

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	TIP32C
▶ Overseas	Part Number	TIP32C
▶ Equivalent	Part Number	TIP32C

EV is the abbreviation of name EVVO

Silicon PNP Epitaxial Transistor

TIP32C

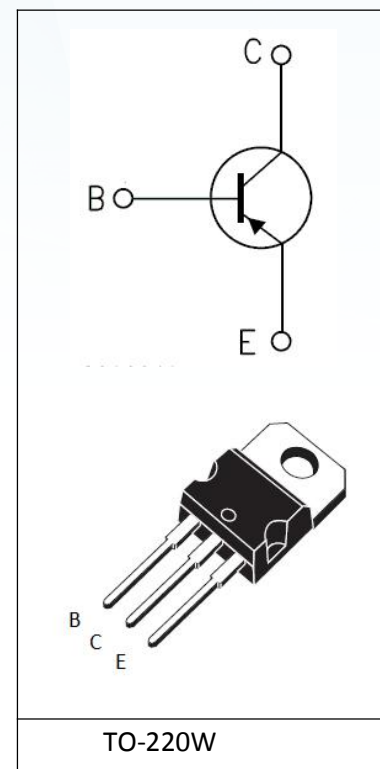
TIP32C, the base island technology PNP power transistor, make this device suitable for audio, power linear and switching applications. The complementary NPN type is TIP31C

Features

- Complementary PNP-NPN devices
- h_{FE} grouping
- h_{FE} improved linearity
- RoHS product

Applications

- General purpose circuits
- Audio amplifier
- Power linear and switching



Absolute Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted):

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current(DC)	I_C	-3	A
Collector Peak Current($t_p < 5\text{ms}$)	I_{CM}	-5	A
Base Current(DC)	I_B	-1	A
Base Peak Current($t_p < 5\text{ms}$)	I_{BM}	-2	A
Collector Power Dissipation	P_C	40	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65~150	$^\circ\text{C}$

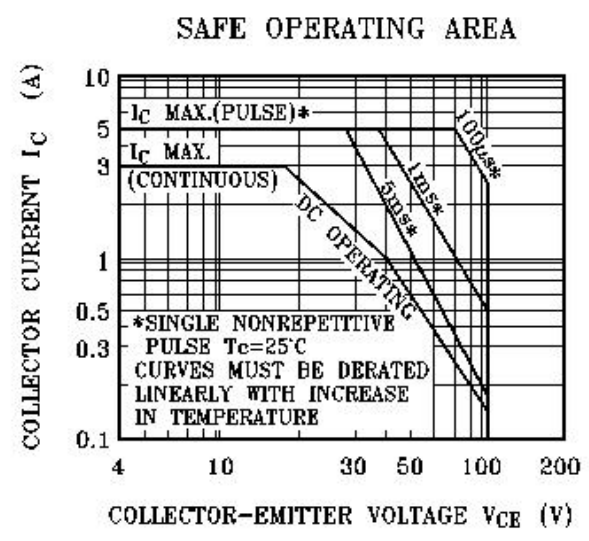
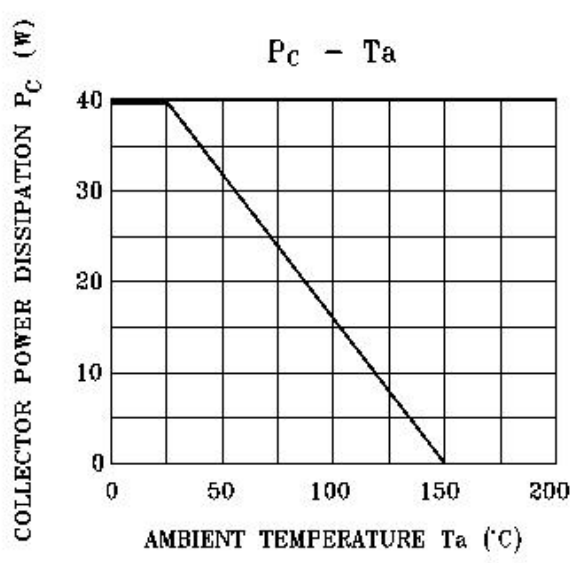
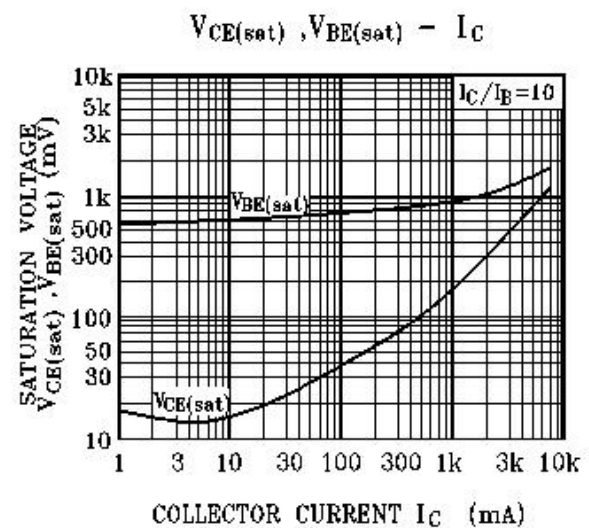
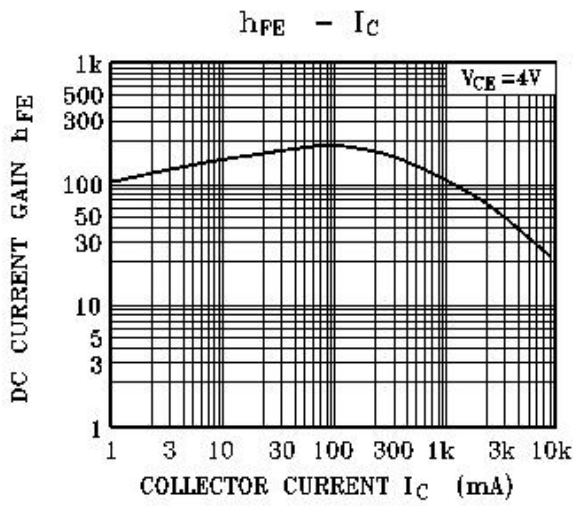
Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted):

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Cut-off Current	I_{CBO}	$V_{CB}=100V, I_E=0$			-0.2	mA
Collector-Emitter Cut-off Current	I_{CEO}	$V_{CE}=100V, I_B=0$			-0.2	mA
Emitter-Base Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$			-1	mA
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$	-100			V
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=1mA$	-100			V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=100uA$	-5			V
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=1A$	25			
	h_{FE2}	$V_{CE}=5V, I_C=3A$	10		50	
Collector-Emitter Saturation Voltage	V_{CEsat}	$I_C=6A, I_B=0.6A$			-1.2	V
Transition Frequency	f_T	$V_{CE}=10V, I_{CE}=0.5A$	3			Mhz

Thermal Characteristics

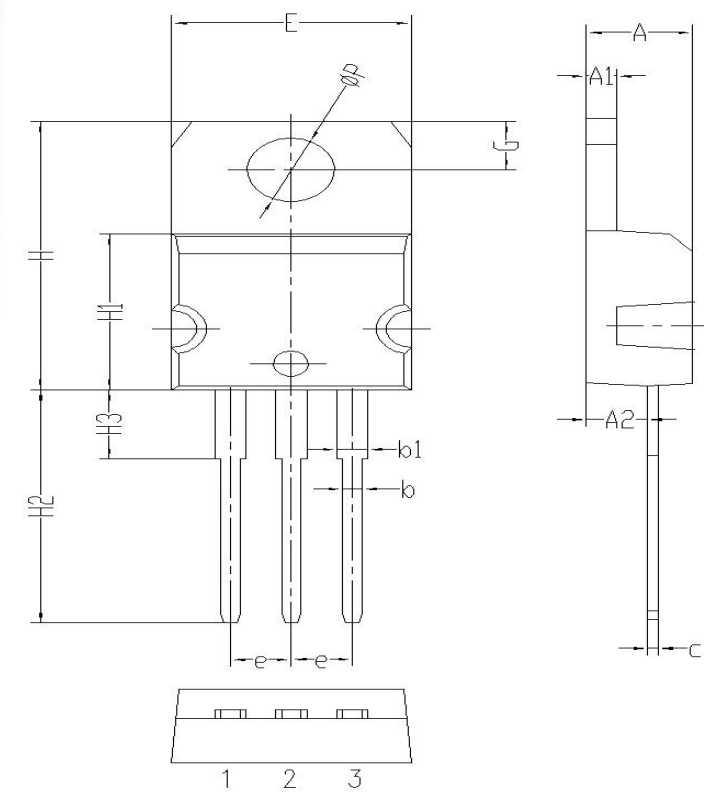
Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	3.0	°C/W

Typical Characteristics



Package Information

TO-220W PACKAGE



Symbol	单位 mm		
	Min	Nom	Max
A	4.05	4.25	4.45
A1	1.2	1.3	1.4
A2	2.35	2.45	2.55
b	0.60	0.8	1.00
b1	1.12	1.32	1.52
c	0.25	0.45	0.65
e	2.34	2.54	2.74
E	9.8	10.0	10.2
H	15.1	15.3	15.5
H1	8.60	8.8	9.00
H2	13.0	13.5	14.0
H3	3.80	4.0	4.20
G	2.60	2.8	3.00
ΦP	3.60	3.8	4.00

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